

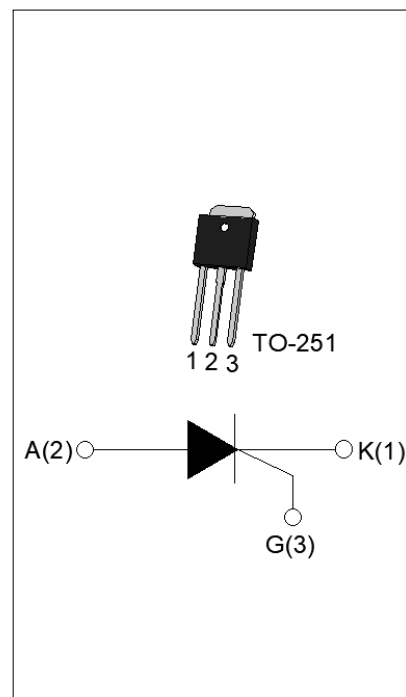


DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT812H of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-251 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	≤ 15	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 63^{\circ}C$)	$I_{T(AV)}$	7.6	A
RMS on-state current ($T_c \leq 63^{\circ}C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^{\circ}C$)	I_{TSM}	140	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^{\circ}C$)		154	
I^2t value for fusing ($t_p=10ms, T_j=25^{\circ}C$)	I^2t	98	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^{\circ}C$)	di/dt	150	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^{\circ}C$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125^{\circ}\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	60	mA
I_H	$I_T=500\text{mA}$	-	-	50	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$	500	-	-	V/ μs
t_{on}	$I_G=20\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^{\circ}\text{C}$	-	5	-	μs
t_{off}		-	80	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=24\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.8	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	27	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.25	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	4	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (DC)	120	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

<u>J</u>	<u>CT</u>	<u>8</u>	<u>12</u>	<u>H</u>
JieJie Microelectronics Co., Ltd.	SCRs			H:TO-251
	$8: V_{DRM} / V_{RRM} \geq 800V$		$I_T(RMS): 12A$	

MARKING

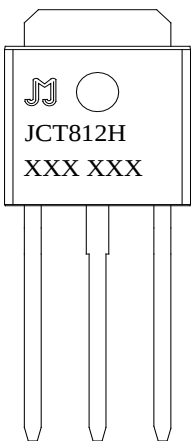
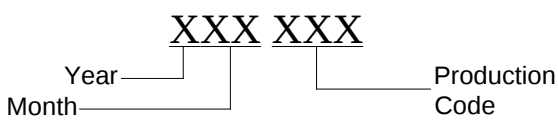
	
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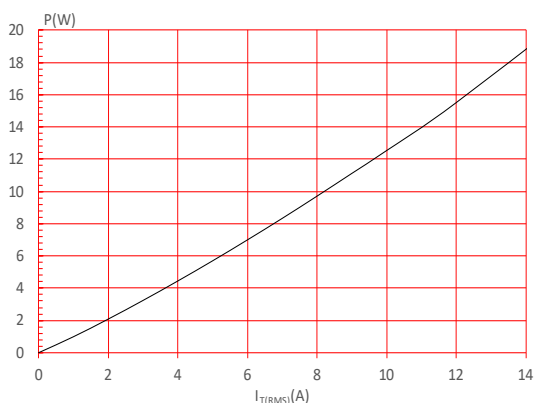
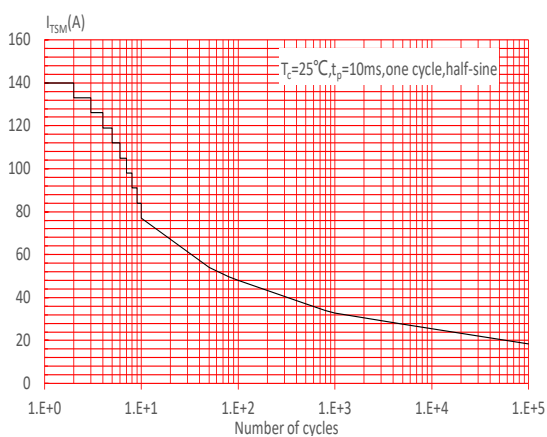
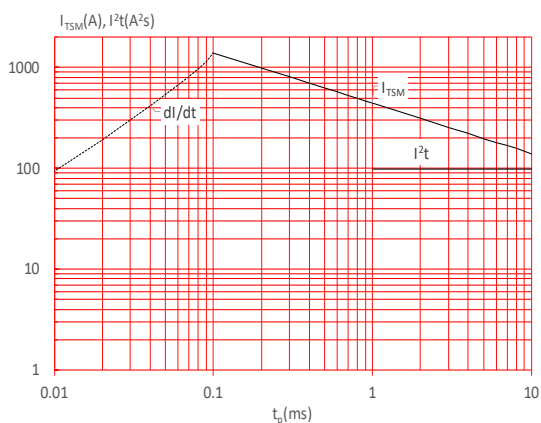
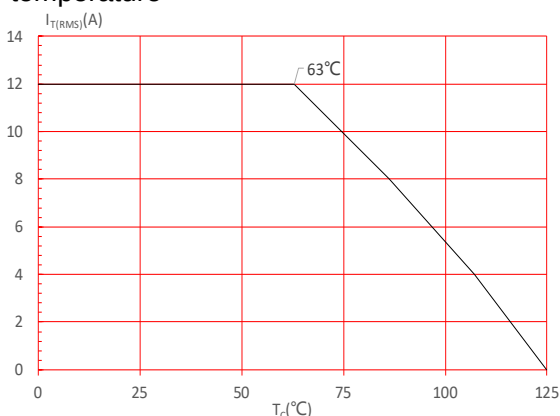
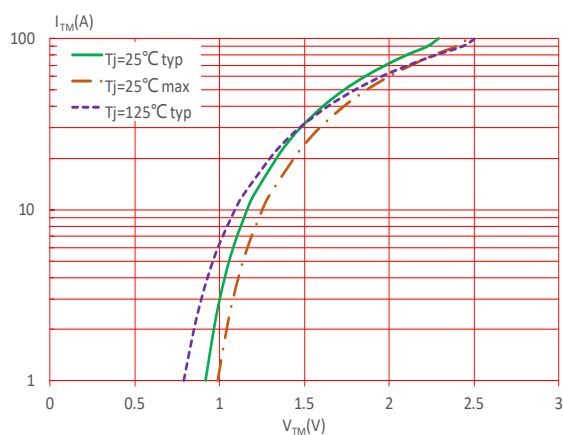
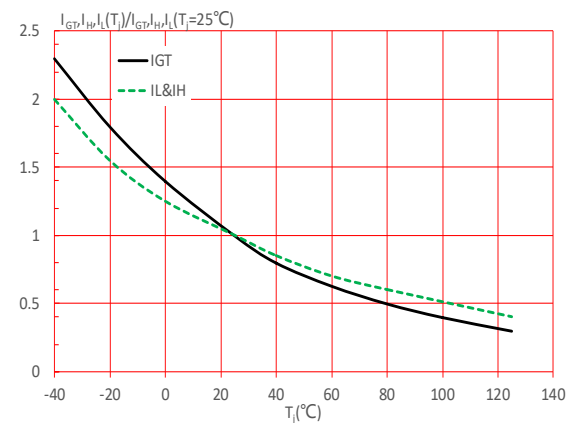
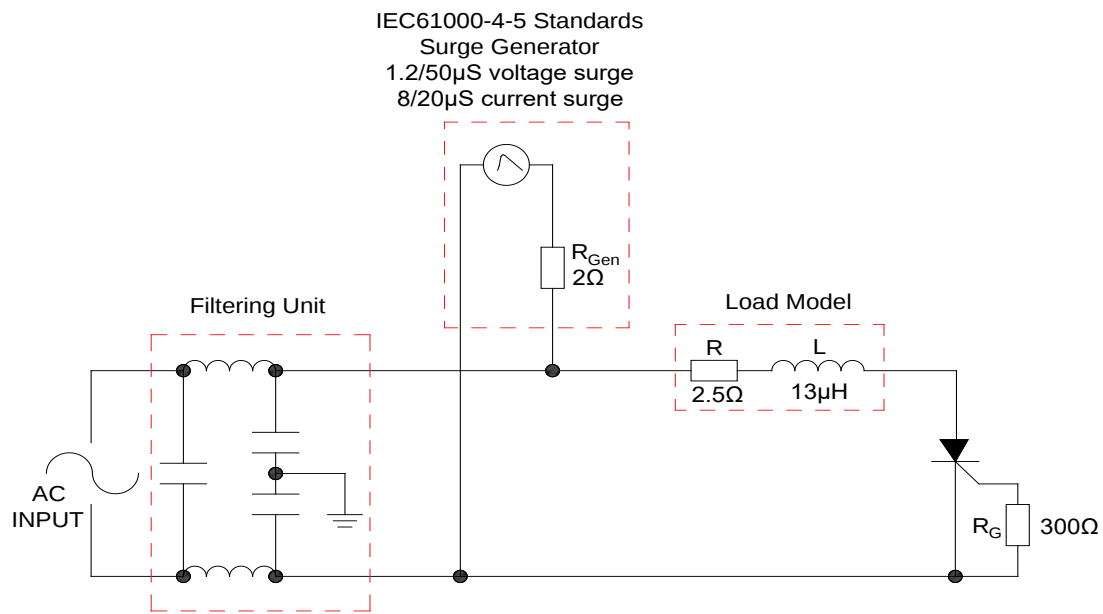
FIG.1: Maximum power dissipation versus RMS on-state current**FIG.3:** Surge peak on-state current versus number of cycles**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of I^2t ($di/dt < 150A/\mu s$)**FIG.2:** RMS on-state current versus case temperature**FIG.4:** On-state characteristics**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie Microelectronics

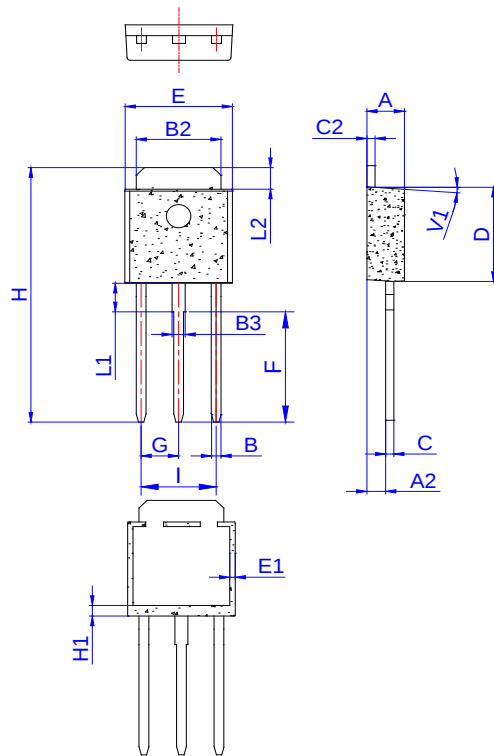
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT812H	800	15	TO-251	80	Tube

Document Revision History

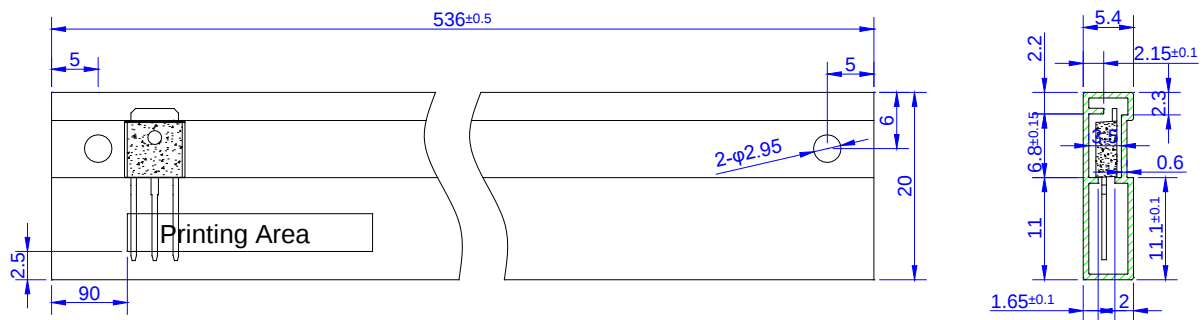
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
E1	0.60		1.00	0.024		0.039
F	6.90		7.30	0.272		0.287
G	2.20		2.40	0.087		0.094
H	16.00		17.00	0.630		0.669
H1	1.45		1.85	0.057		0.073
I	4.40		4.80	0.173		0.189
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1		4°			4°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-251	TUBE	80	4,000	20,000

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